## 80V, 300mA Three Phase High Side Driver

The HIP4083 is a three phase high side N-channel MOSFET driver, specifically targeted for PWM motor control. Two HIP4083 may be used together for 3 phase full bridge applications (see application block diagram). Alternatively, the lower gates may be controlled directly from a buffered microprocessor output.

Unlike other members of the HIP408x family, the HIP4083 has no built in turn-on delay. Each output (AHO, BHO, and CHO ) will turn-on 65 ns after its input is switched low. Likewise, each output will turn-off 60ns after its input is switched high. Very short and very long dead times are possible when two HIP4083 are used to drive a full bridge. This dead time is controlled by the input signal timing.

The HIP4083 does not have a built in charge pump. Therefore, the bootstrap capacitors must be recharged on a periodic basis by initiating a short refresh pulse. In most bridge applications, this will happen automatically every time the lower FETs turn-on and the upper FETs turn-off. However, it is still possible to use the HIP4083 in applications that require the high side FETs to be on for extended periods of time. This can be easily accomplished by sending a short refresh pulse to the DIS pin.

The HIP4083 has reduced drive current compared to the HIP4086 making it ideal for low to moderate power applications. The HIP4083 is optimized for applications where size and cost are important. For high power applications driving large power FETs, the HIP4086 is recommended.

## Pinout

HIP4083
(PDIP, SOIC)
TOP VIEW


## Features

- Independently Drives Three High Side N-Channel MOSFETs in Three Phase Bridge Configuration
- Bootstrap Supply Max Voltage to 95VDC
- Bias Supply Operation from 7V to 15 V
- Drives 1000pF Load with Typical Rise Times of 35ns and Fall Times of 30ns
- CMOS/TTL Compatible Inputs
- Programmable Undervoltage Protection
- Pb-free Available


## Applications

- Brushless Motors
- High Side Switches
- AC Motor Drives
- Switched Reluctance Motor Drives


## Ordering Information

| PART NUMBER | TEMP. <br> RANGE $\left({ }^{\circ} \mathbf{C}\right)$ | PACKAGE | PKG. <br> DWG. \# |
| :--- | :--- | :--- | :--- |
| HIP4083AB | -40 to 105 | 16 Ld SOIC | M16.15 |
| HIP4083ABZ (Note) | -40 to 105 | 16 Ld SOIC (Pb-free) | M16.15 |
| HIP4083AP | -40 to 105 | 16 Ld PDIP | E16.3 |
| HIP4083APZ (Note) | -40 to 105 | 16 Ld PDIP (Pb-free) | E16.3 |

NOTE: Intersil Pb-free products employ special Pb-free material sets; molding compounds/die attach materials and $100 \%$ matte tin plate termination finish, which is compatible with both SnPb and Pb -free soldering operations. Intersil Pb -free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb -free requirements of IPC/JEDEC J Std-020B.

## Application Block Diagram



## Functional Block Diagram



TRUTH TABLE

| INPUT |  | OUTPUT |  |
| :---: | :---: | :---: | :---: |
| $\overline{\mathbf{A H I}, \mathbf{B H I}, \mathbf{C H I}}$ | UV | DIS | AHO, BHO, CHO |
| $X$ | 1 | X | 0 |
| X | X | 1 | 0 |
| 1 | 0 | 0 | 0 |
| 0 | 0 | 0 | 1 |

NOTE: X signifies that input can be either a " 1 " or " 0 ".

## Typical Application: Three Phase Bridge Driver with Programmable Dead Time



## Typical Application: High Side Switch



## Pin Descriptions

| PIN NUMBER | SYMBOL | DESCRIPTION |
| :---: | :---: | :---: |
| $\begin{gathered} \hline 6 \\ 11 \\ 16 \end{gathered}$ | AHB <br> BHB <br> CHB <br> (xHB) | Gate driver supplies. One external bootstrap diode and one capacitor are required for each. The bootstrap diode and capacitor may be omitted when the HIP4083 is used to drive the lower gates in three phase full bridge applications. In this case, tie all three xHB pins to $\mathrm{V}_{\text {DD }}$ and tie the xHS pins to the sources of the lower FETs. In full bridge applications, the lower FETs must be turned on first at start up to refresh the bootstrap capacitors. In high side switch applications, the load will keep xHS low and refresh should happen automatically at start up. |
| $\begin{aligned} & 1 \\ & 2 \\ & 3 \end{aligned}$ | AHI <br> BHI <br> CHI <br> (xHI) | Logic level inputs. Logic at these three pins controls the three output drivers, $\mathrm{AHO}, \mathrm{BHO}$ and CHO . When $\overline{\mathrm{xHI}}$ is low, xHO is high. When $\overline{\mathrm{xHI}}$ is high, xHO is low. DIS (Disable) overrides all input signals. $\overline{\mathrm{xHI}}$ can be driven by signal levels of 0 V to 15 V (no greater than $\mathrm{V}_{\mathrm{DD}}$ ). |
| 5 | $\mathrm{V}_{\text {SS }}$ | Chip ground. |
| 13 | UVLO | Undervoltage setting. A resistor can be connected between this pin and $\mathrm{V}_{S S}$ to program the under voltage set point - see Figure 7. With this pin not connected the undervoltage set point is typically 7 V . When this pin is tied to $\mathrm{V}_{\mathrm{DD}}$, the undervoltage set point is typically 6.2 V . |
| 4 | DIS | Disable input. Logic level input that when taken high sets all three outputs low. DIS high overrides all other inputs. When DIS is taken low the outputs are controlled by the other inputs. DIS can be driven by signal levels of 0 V to 15 V (no greater than $\mathrm{V}_{\mathrm{DD}}$ ). |
| $\begin{gathered} 7 \\ 10 \\ 15 \end{gathered}$ | AHO <br> BHO <br> CHO <br> (xHO) | Gate connections. Connect to the gates of the power MOSFETs in each phase. |
| $\begin{gathered} 8 \\ 9 \\ 14 \end{gathered}$ | AHS <br> BHS <br> CHS <br> (xHS) | MOSFET source connection. Connect the sources of the power MOSFETs and the negative side of the bootstrap capacitors to these pins. In high side switch applications, 2 mA of current will flow out of these pins into the load when the upper FETs are off. This current is necessary to guarantee that the upper FETs stay off. This current tends to pull xHS high. For proper refresh, the load must pull the voltage on xHS down to at least 7 V below $\mathrm{V}_{\mathrm{DD}}$. For example, when $\mathrm{V}_{\mathrm{DD}}=12 \mathrm{~V}$, xHS must be pulled down to 5 V . Therefore, the minimum load necessary for proper refresh is given by the following equation: $R_{\text {MIN }}=5 \mathrm{~V} / 2 \mathrm{~mA}=2.5 \mathrm{k} \Omega$. So in this case, if the load has an impedance less than $5 \mathrm{k} \Omega$, refresh will happen automatically at start up. |
| 12 | $\mathrm{V}_{\mathrm{DD}}$ | Positive supply rail. Bypass this pin to $\mathrm{V}_{S S}$ with a capacitor $\geq 1 \mu \mathrm{~F}$. In applications where the bus voltage and chip $V_{D D}$ are at the same potential, it is a good idea to run a separate line from the supply to each. This greatly simplifies the filtering requirements. |


| Absolute Maximum Ratings $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ |  |
| :---: | :---: |
| Supply Voltage, V ${ }_{\text {DD }}$ | 3 V to 16 V |
| Logic I/O Voltages | -0.3V to $\mathrm{V}_{\mathrm{DD}}+0.3 \mathrm{~V}$ |
| Voltage on xHS | nt) to $85 \mathrm{~V}\left(-40^{\circ} \mathrm{C}\right.$ to $\left.150^{\circ} \mathrm{C}\right)$ |
| Voltage on xHB | $\mathrm{V}_{\mathrm{xHS}}-0.3 \mathrm{~V}$ to $\mathrm{V}_{\mathrm{xHS}}+\mathrm{V}_{\mathrm{DD}}$ |
| Voltage on xLO | $\mathrm{V}_{\mathrm{SS}}-0.3 \mathrm{~V}$ to $\mathrm{V}_{\mathrm{DD}}+0.3 \mathrm{~V}$ |
| Voltage on xHO | $\mathrm{V}_{\mathrm{xHS}}-0.3 \mathrm{~V}$ to $\mathrm{V}_{\mathrm{xHB}}+0.3 \mathrm{~V}$ |
| Phase Slew Rate | 20V/ns |

## Thermal Information

| Thermal Resistance (Typical, Note 1) | $\theta_{\mathrm{JA}}\left({ }^{\circ} \mathrm{C} / \mathrm{W}\right)$ |
| :---: | :---: |
| SOIC Package. | 100 |
| DIP Package | 80 |
| Maximum Storage Temperature Range | $-65^{\circ} \mathrm{C}$ to $150^{\circ} \mathrm{C}$ |
| Maximum Junction Temperature | $150^{\circ} \mathrm{C}$ |
| Maximum Lead Temperature (Soldering 10s) (SOIC - Lead Tips Only) | $300^{\circ} \mathrm{C}$ |

## Operating Conditions



Voltage on xHS . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . 0 V to 80 V
Voltage on xHB . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . $V_{x H S}+V_{D D}$
Operating Ambient Temperature Range . . . . . . . . . . $-40^{\circ} \mathrm{C}$ to $125^{\circ} \mathrm{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.
NOTES:

1. $\theta_{\mathrm{JA}}$ is measured with the component mounted on an evaluation PC board in free air.
2. All voltages are relative to $\mathrm{V}_{\mathrm{SS}}$ unless otherwise specified.
3. $x=A, B$ and $C$. For example, $x H S$ refers to AHS, BHS and CHS.

## Electrical Specifications $\quad V_{D D}=V_{x H B}=12 \mathrm{~V}, \mathrm{~V}_{\mathrm{SS}}=\mathrm{V}_{\mathrm{xHS}}=0 \mathrm{~V}$, Gate Capacitance $\left(\mathrm{C}_{\mathrm{GATE}}\right)=1000 \mathrm{pF}, \mathrm{R}_{\mathrm{UV}}=\infty$

| PARAMETER | TEST CONDITIONS | $\mathrm{T}_{\mathrm{J}}=25^{\circ} \mathrm{C}$ |  |  | $\begin{gathered} \mathrm{T}_{\mathrm{J}}=-40^{\circ} \mathrm{C} \text { TO } \\ 150^{\circ} \mathrm{C} \end{gathered}$ |  | UNITS |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | MIN | TYP | MAX | MIN | MAX |  |
| SUPPLY CURRENTS AND UNDER VOLTAGE PROTECTION |  |  |  |  |  |  |  |
| $\mathrm{V}_{\text {DD }}$ Quiescent Current | $\overline{\mathrm{xHI}}=5 \mathrm{~V}$ | 0.5 | 1.5 | 2.25 | 0.25 | 2.3 | mA |
| $\mathrm{V}_{\text {DD }}$ Operating Current | $\mathrm{f}=20 \mathrm{kHz}, 50 \%$ Duty Cycle | 1.0 | 2.0 | 2.5 | 0.75 | 3.0 | mA |
| xHB On Quiescent Current | $\overline{\mathrm{xHI}}=0 \mathrm{~V}$ | 65 | 100 | 240 | 45 | 250 | $\mu \mathrm{A}$ |
| xHB Off Quiescent Current | $\overline{\mathrm{xHI}}=5 \mathrm{~V}$ | 0.6 | 0.85 | 1.3 | 0.5 | 1.4 | mA |
| xHB Operating Current | $\mathrm{f}=20 \mathrm{kHz}, 50 \%$ Duty Cycle | 0.6 | 0.85 | 1.2 | 0.5 | 1.3 | mA |
| $\mathrm{V}_{\text {DD }}$ Rising Undervoltage Threshold | RUV OPEN | 6.2 | 7.0 | 8.0 | 6.1 | 8.1 | V |
| $V_{\text {DD }}$ Falling Undervoltage Threshold | Ruv OPEN | 5.75 | 6.5 | 7.5 | 5.25 | 7.6 | V |
| Minimum Undervoltage Threshold | $\mathrm{R}_{\mathrm{UV}}=\mathrm{V}_{\mathrm{DD}}$ | 5.0 | 6.2 | 6.9 | 4.5 | 7.0 | V |
| INPUT PINS: AHI, BHI, CHI AND DIS |  |  |  |  |  |  |  |
| Low Level Input Voltage |  | - | - | 1.0 | - | 0.8 | V |
| High Level Input Voltage |  | 2.5 | - | - | 2.7 | - | V |
| Input Voltage Hysteresis |  | - | 35 | - | - | - | mV |
| Low Level Input Current | $\mathrm{V}_{\mathrm{IN}}=0 \mathrm{~V}$ | -145 | -100 | -60 | -150 | -50 | $\mu \mathrm{A}$ |
| High Level Input Current | $\mathrm{V}_{\mathrm{IN}}=5 \mathrm{~V}$ | -1 | - | +1 | -10 | +10 | $\mu \mathrm{A}$ |

## GATE DRIVER OUTPUT PINS: AHO, BHO, AND CHO

| Average Turn-On Current | $\mathrm{V}_{\text {OUT }}$ OV to 5V | 100 | 240 | 400 | 50 | 500 | mA |
| :--- | :--- | :--- | :--- | :--- | :--- | :--- | :--- |
| Average Turn-Off Current | $\mathrm{V}_{\text {OUT }} \mathrm{V}_{\text {DD }}$ to 4 V | 150 | 300 | 450 | 100 | 550 | mA |

Switching Specifications $V_{D D}=V_{x H B}=12 \mathrm{~V}, \mathrm{~V}_{\mathrm{SS}}=\mathrm{V}_{\mathrm{xHS}}=0 \mathrm{~V}, \mathrm{C}_{\mathrm{GATE}}=1000 \mathrm{pF}$

| PARAMETER | TEST CONDITIONS | $\mathrm{T}_{\mathrm{J}}=25^{\circ} \mathrm{C}$ |  |  | $\begin{gathered} \mathrm{T}_{\mathrm{JS}}=-40^{\circ} \mathrm{C} \mathrm{TO} \\ 150^{\circ} \mathrm{C} \end{gathered}$ |  | UNITS |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | MIN | TYP | MAX | MIN | MAX |  |
| Turn-Off Propagation Delay ( $\mathrm{xHI}-\mathrm{xHO}$ ) | No Load | - | 60 | 80 |  | 90 | ns |
| Turn-On Propagation Delay ( $\mathrm{xHI}-\mathrm{xHO}$ ) | No Load | - | 65 | 90 |  | 100 | ns |
| Rise Time (10-90\%) | $\mathrm{C}_{\text {GATE }}=1000 \mathrm{pF}$ | - | 35 | 60 | - | 65 | ns |
| Fall Time (90-10\%) | $\mathrm{C}_{\text {GATE }}=1000 \mathrm{pF}$ | - | 30 | 50 | - | 55 | ns |
| Disable Turn-Off Propagation Delay | No Load | - | 65 | - | - | 100 | ns |
| Disable to Output Enable (DIS - xHO) | No Load | - | 70 | - | - | 100 | ns |

## Typical Performance Curves



FIGURE 1. $\mathrm{V}_{\mathrm{DD}}$ SUPPLY CURRENT vs $\mathrm{V}_{\mathrm{DD}}$ SUPPLY VOLTAGE


FIGURE 3. FLOATING SUPPLY OFF BIAS CURRENT


FIGURE 2. $V_{D D}$ SUPPLY CURRENT vs SWITCHING FREQUENCY


FIGURE 4. FLOATING SUPPLY ON BIAS CURRENT

## Typical Performance Curves (Continued)



FIGURE 5. FLOATING SUPPLY SWITCHING BIAS CURRENT


FIGURE 7. UNDERVOLTAGE THRESHOLD


FIGURE 9. RISE AND FALL TIME (10-90\%)


FIGURE 6. FLOATING SUPPLY SWITCHING BIAS CURRENT


FIGURE 8. PROPAGATION DELAY


FIGURE 10. GATE DRIVER AVERAGE TURN-ON CURRENT

## Typical Performance Curves (Continued)



FIGURE 11. GATE DRIVER AVERAGE TURN-OFF CURRENT


FIGURE 12. HIGH VOLTAGE LEAKAGE CURRENT

Dual-In-Line Plastic Packages (PDIP)


-     -         - 



NOTES:

1. Controlling Dimensions: INCH. In case of conflict between English and Metric dimensions, the inch dimensions control.
2. Dimensioning and tolerancing per ANSI Y14.5M-1982.
3. Symbols are defined in the "MO Series Symbol List" in Section 2.2 of Publication No. 95.
4. Dimensions $A, A 1$ and $L$ are measured with the package seated in JEDEC seating plane gauge GS-3.
5. D, D1, and E1 dimensions do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.010 inch ( 0.25 mm ).
6. E and $\mathrm{e}_{\mathrm{A}}$ are measured with the leads constrained to be perpendicular to datum $-\mathrm{C}-$.
7. $e_{B}$ and $e_{C}$ are measured at the lead tips with the leads unconstrained. $e_{C}$ must be zero or greater.
8. B1 maximum dimensions do not include dambar protrusions. Dambar protrusions shall not exceed 0.010 inch $(0.25 \mathrm{~mm})$.
9. N is the maximum number of terminal positions.
10. Corner leads ( $1, \mathrm{~N}, \mathrm{~N} / 2$ and $\mathrm{N} / 2+1$ ) for E8.3, E16.3, E18.3, E28.3, E42.6 will have a B1 dimension of 0.030-0.045 inch (0.76-1.14mm).

E16.3 (JEDEC MS-001-BB ISSUE D)
16 LEAD DUAL-IN-LINE PLASTIC PACKAGE

| SYMBOL | INCHES |  | MILLIMETERS |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  | MIN | MAX | MIN | MAX |  |
| A | - | 0.210 | - | 5.33 | 4 |
| A1 | 0.015 | - | 0.39 | - | 4 |
| A2 | 0.115 | 0.195 | 2.93 | 4.95 | - |
| B | 0.014 | 0.022 | 0.356 | 0.558 | - |
| B1 | 0.045 | 0.070 | 1.15 | 1.77 | 8,10 |
| C | 0.008 | 0.014 | 0.204 | 0.355 | - |
| D | 0.735 | 0.775 | 18.66 | 19.68 | 5 |
| D1 | 0.005 | - | 0.13 | - | 5 |
| E | 0.300 | 0.325 | 7.62 | 8.25 | 6 |
| E1 | 0.240 | 0.280 | 6.10 | 7.11 | 5 |
| e | $0.100 ~ B S C$ | $2.54 ~ B S C$ | - |  |  |
| $\mathrm{e}_{\mathrm{A}}$ | 0.300 BSC | 7.62 BSC |  | 6 |  |
| $\mathrm{e}_{\mathrm{B}}$ | - | 0.430 | - | 10.92 | 7 |
| L | 0.115 | 0.150 | 2.93 | 3.81 | 4 |
| N | 16 |  | 16 |  | 9 |

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M16.15 (JEDEC MS-012-AC ISSUE C)
16 LEAD NARROW BODY SMALL OUTLINE PLASTIC PACKAGE

NOTES:

1. Symbols are defined in the "MO Series Symbol List" in Section 2.2 of Publication Number 95.
2. Dimensioning and tolerancing per ANSI Y14.5M-1982.
3. Dimension " $D$ " does not include mold flash, protrusions or gate burrs. Mold flash, protrusion and gate burrs shall not exceed 0.15 mm ( 0.006 inch) per side.
4. Dimension "E" does not include interlead flash or protrusions. Interlead flash and protrusions shall not exceed 0.25 mm ( 0.010 inch) per side.
5. The chamfer on the body is optional. If it is not present, a visual index feature must be located within the crosshatched area.
6. " $L$ " is the length of terminal for soldering to a substrate.
7. " N " is the number of terminal positions.
8. Terminal numbers are shown for reference only.
9. The lead width " $B$ ", as measured 0.36 mm ( 0.014 inch ) or greater above the seating plane, shall not exceed a maximum value of 0.61 mm ( 0.024 inch)
10. Controlling dimension: MILLIMETER. Converted inch dimensions are not necessarily exact.

| SYMBOL | INCHES |  | MILLIMETERS |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  | MIN | MAX | MIN | MAX |  |
| A | 0.053 | 0.069 | 1.35 | 1.75 | - |
| A1 | 0.004 | 0.010 | 0.10 | 0.25 | - |
| B | 0.014 | 0.019 | 0.35 | 0.49 | 9 |
| C | 0.007 | 0.010 | 0.19 | 0.25 | - |
| D | 0.386 | 0.394 | 9.80 | 10.00 | 3 |
| E | 0.150 | 0.157 | 3.80 | 4.00 | 4 |
| e | 0.050 |  | BSC | 1.27 |  |
| BSC | - |  |  |  |  |
| H | 0.228 | 0.244 | 5.80 | 6.20 | - |
| h | 0.010 | 0.020 | 0.25 | 0.50 | 5 |
| L | 0.016 | 0.050 | 0.40 | 1.27 | 6 |
| N | 16 |  | 16 |  | 7 |
| $\alpha$ | $0^{\circ}$ | $8^{\circ}$ | $0^{\circ}$ | $8^{\circ}$ | - |

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